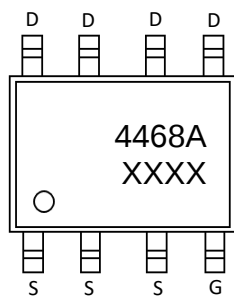


Features

- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application

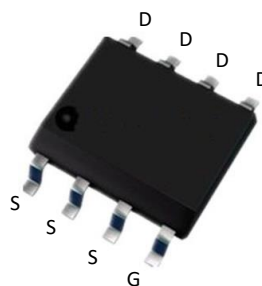


Marking and pin assignment

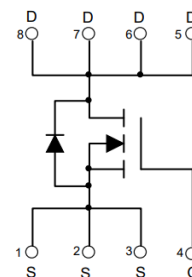
4468A : Device code
XXXX : Code

30V/10.5A N-Channel MOSFET Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
30V	19mΩ@10V	10.5A
	27mΩ@4.5V	



SOP-8 top view



Schematic diagram



Pb-Free



RoHS



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)				
Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
V _{DS}	Drain-Source Breakdown Voltage		30	V
V _{GS}	Gate-Source Voltage		±20	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	10.5	A
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested	Tc=25°C	50	A
I _D	Continuous Drain Current	Tc=25°C	10.5	A
P _D	Maximum Power Dissipation	Tc=25°C	2.5	W
R _{θJA}	Thermal Resistance Junction-Ambient		75	°C/W

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V	--	--	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =10.5A	--	14	19	mΩ
		V _{GS} =4.5V, I _D =9A	--	20	27	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	--	572	--	pF
C _{OSS}	Output Capacitance		--	81	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	65	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DD} =15V, I _D =10A, V _{GS} =10V	--	6.2	--	nC
Q _{gs}	Gate Source Charge		--	2.4	--	nC
Q _{gd}	Gate Drain Charge		--	2.5	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =30V, I _D =10A, V _{GS} =10V, R _G =3Ω	--	3	--	nS
t _r	Turn-on Rise Time		--	7.5	--	nS
t _{d(off)}	Turn-Off Delay Time		--	20	--	nS
t _f	Turn-Off Fall Time		--	4	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25℃, I _S =10.5A,	--	0.8	1.2	V

Typical Operating Characteristics

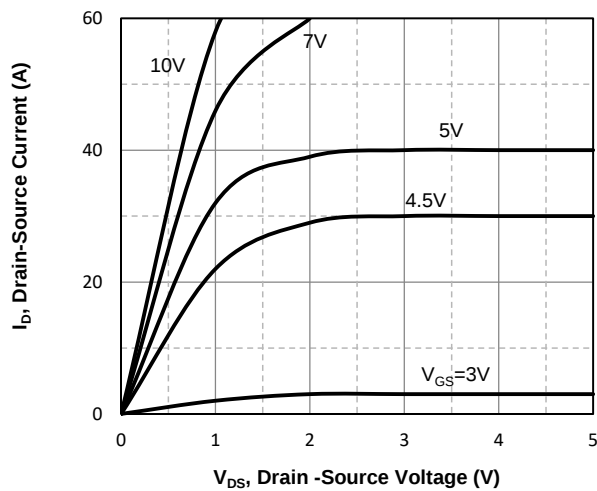


Fig1. Typical Output Characteristics

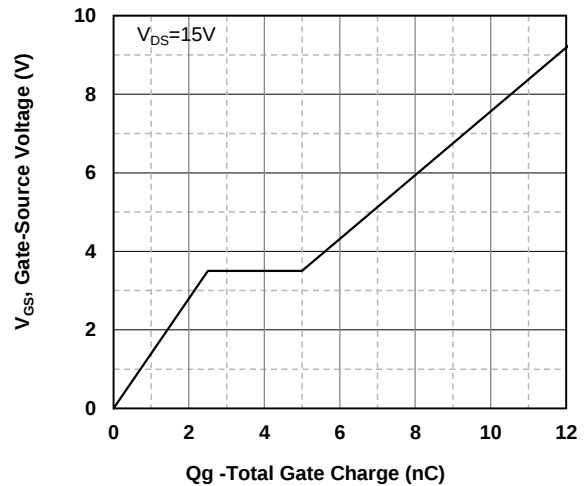


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

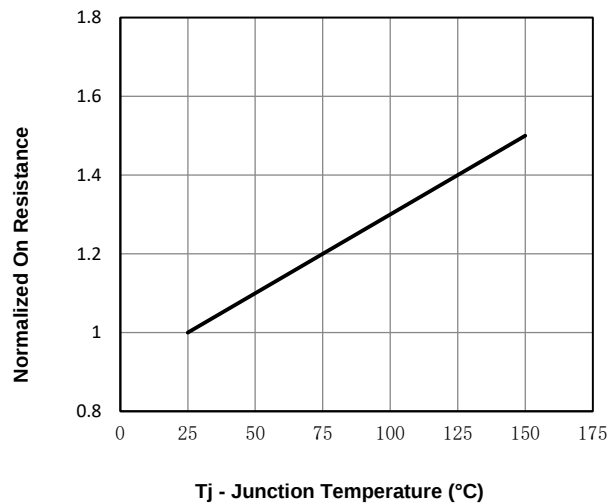


Fig3. Normalized On-Resistance Vs. Temperature

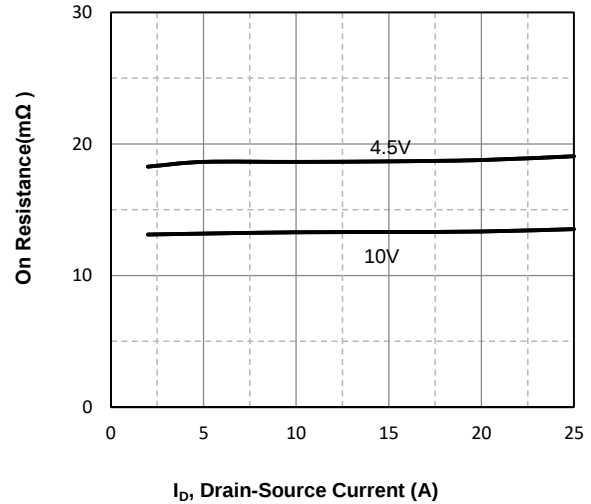


Fig4. On-Resistance Vs. Drain-Source Current

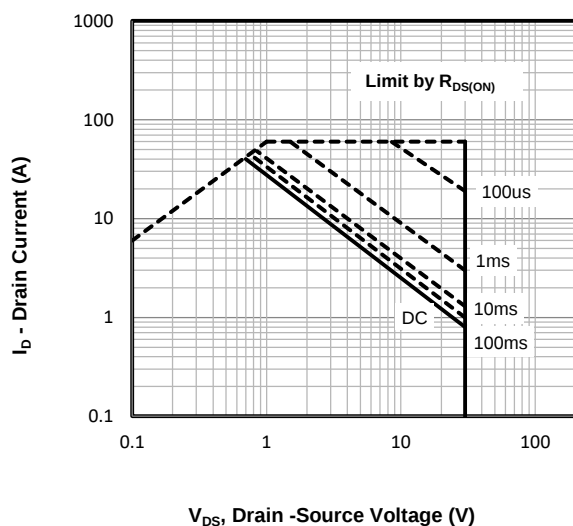


Fig5. Maximum Safe Operating Area

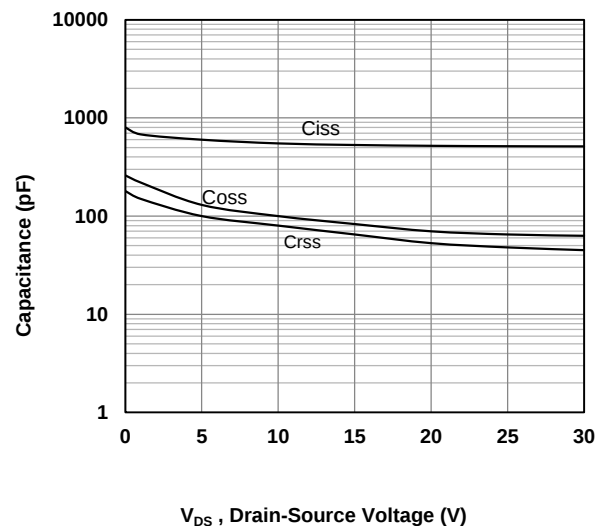
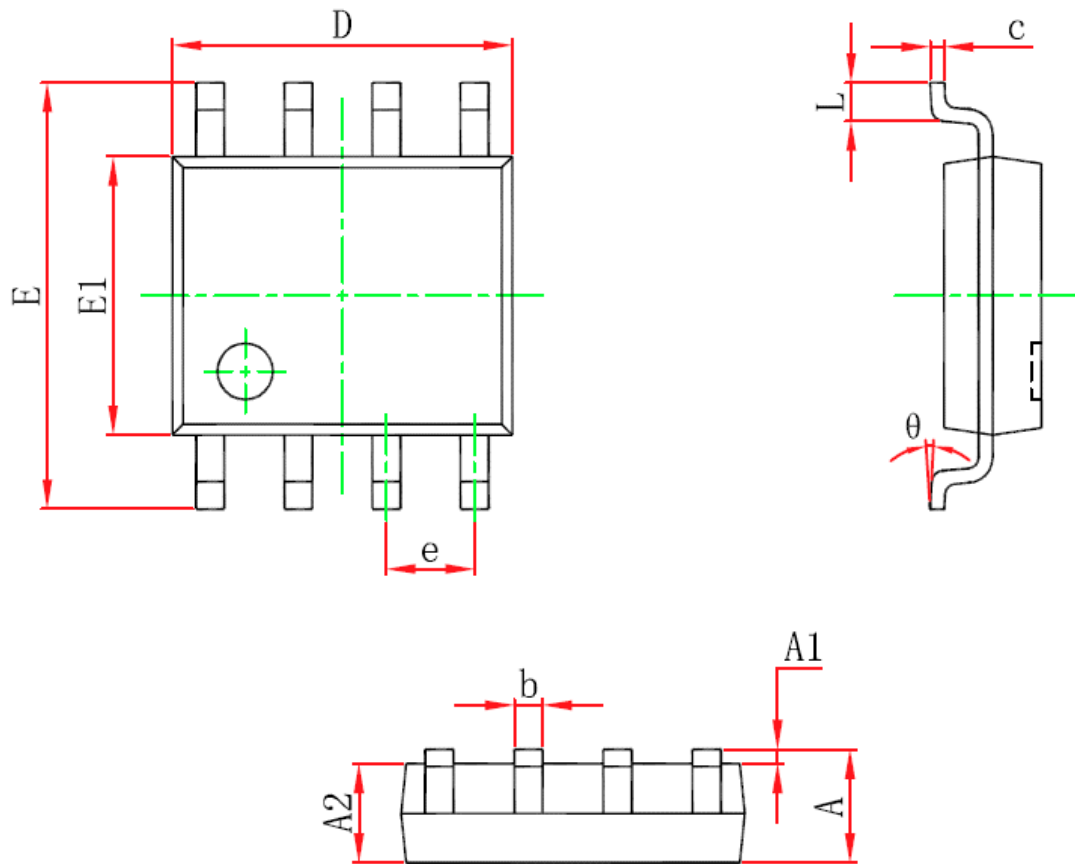


Fig6 Typical Capacitance Vs. Drain-Source

SOP-8 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.700	5.100	0.185	0.201
e	1.270(BSC)		0.050(BSC)	
E	5.800	6.200	0.028	0.035
E1	3.800	4.000	0.057	0.069
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°